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(c) heating said multilayer structure at a temperature less than 600°C to remove said first and second combinations of organic materials and their decomposition products, such as carbon, to levels below 200 ppm; thereafter

(d) sintering at a temperature from about 600°C to about 1050°C at a partial pressure of oxygen from about 10^{-3} to 10^{-15} atm to produce said multilayer piezoelectric device with alternating piezoelectric ceramic layers and base metal layers as electrodes .

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12. (Amended) The device of claim 10, wherein said base metal is selected from the group consisting of Cu, Ni and alloys thereof.

13. (Amended) The device of claim 10, wherein said first combination of organic materials includes binder, solvents, plasticizers, dispersants, and combinations thereof.

14. (Amended) The device of claim 10, wherein said second combination of organic materials includes solvents, binder, and combinations thereof.
